AMENDMENT TO THE CLAIMS

This listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

1. (Currently Amended) A production method for producing a light-emitting device in which a light-emitting layer at least including [[a]] an n-type semiconductor layer and a p-type semiconductor layer is layered on a transparent crystal substrate, comprising ~~the steps of~~:

applying a silicon organic solvent to at least a part of the transparent crystal substrate or the light-emitting layer to form ~~forming~~ a transfer layer on at least a part of the transparent crystal substrate or the light-emitting layer~~, which transfer layer is softened or set~~

softening or setting said transfer layer upon supplying an energy thereto;

pressing a mold formed with a minute unevenness structure against the transfer layer to transfer the minute unevenness structure to an outer surface of the transfer layer under a pressure of 5 MPa or higher and 150 MPa or lower; and

dry etching the transfer layer with a chlorine gas using the transfer layer as a resist mask to form ~~forming~~ a minute unevenness structure for preventing multiple reflection ~~based on the minute unevenness structure transferred to the transfer layer~~ in the transparent crystal substrate or the light-emitting layer.

2. (Currently Amended) A production method according to claim 1, wherein ~~the step of~~ forming the minute unevenness structure in the light-emitting layer includes ~~a step of~~ separating

the transparent crystal substrate from the light-emitting layer after a substrate bearing layer is formed on a surface of the light-emitting layer where electrodes are to be formed.

3. (Canceled)

4. (Currently Amended) A production method according to claim ~~3~~ 1, wherein ~~the step of~~ forming the minute unevenness structure for preventing the multiple reflection in the light-emitting layer includes ~~a step of~~ pressing a mold having an upper flat portion to be located near the bottoms of the minute unevenness structure for preventing the multiple reflection and a lower flat portion to be located at a position lowered from the upper flat portion by about the thickness of the upper semiconductor layer of the light-emitting layer against the transfer layer to transfer an upper flat portion and a lower flat portion together with the minute unevenness structure to the transfer layer, and forming electrode-forming portions by etching the upper and lower semiconductor layers of the light-emitting layer when dry etching is carried out using the transfer layer as a resist mask.

5. (Currently Amended) A production method according to claim 4, wherein the etching ~~step includes a step of~~ comprises adjusting a selection ratio of the etching speed of the light-emitting layer to that of the resist from twofold to fourfold.

6. (Currently Amended) A production method according to claim 5, wherein ~~the step of~~ applying the silicon organic solvent to form the transfer layer ~~includes a step of~~ comprises applying the silicon organic solvent by potting or spray coating.

7. (Canceled)

8. (Currently Amended) A production method according to claim 6, ~~7, wherein a step of~~ comprising forming an unevenness structure larger than the minute unevenness structure on the minute unevenness structure of the light-emitting layer ~~is carried out~~ after ~~the step of~~ forming the minute unevenness structure for preventing the multiple reflection in the light-emitting layer.

9. (Original) A production method according to claim 8, wherein the unevenness structure has the shape of a prism or microlens.

10. (Currently Amended) A production method according to claim ~~3~~ 1, wherein the etching ~~step includes a step of~~ comprises adjusting a selection ratio of the etching speed of the light-emitting layer to that of the resist from twofold to fourfold.

11. (Canceled)

12. (Currently Amended) A production method according to claim ~~3~~ 1, ~~wherein a step of~~ comprising forming an unevenness structure larger than the minute unevenness structure on the minute unevenness structure of the light-emitting layer ~~is carried out~~ after ~~the step of~~ forming the minute unevenness structure for preventing the multiple reflection in the light-emitting layer.

13. (Canceled)

14. (Currently Amended) A production method according to claim 1, wherein ~~the step of~~ applying the silicon organic solvent to form the transfer layer ~~includes a step of~~ comprises applying the silicon organic solvent by potting or spray coating.